

# PRELIMINARY

Notice : This is not a final specification  
Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR <GaAs MMIC>

# MGFC5108

Ka-Band 3-Stage Self Bias Low Noise Amplifier

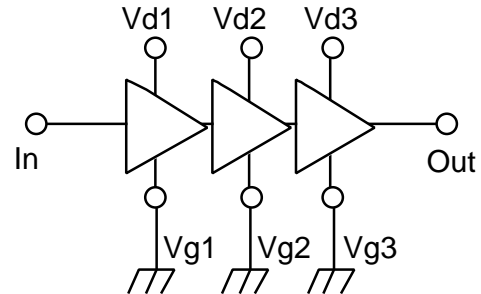
## DESCRIPTION

The MGFC5108 is a GaAs MMIC chip especially designed for 24.0 ~ 27.0 GHz band Low Noise Amplifier.(LNA) .

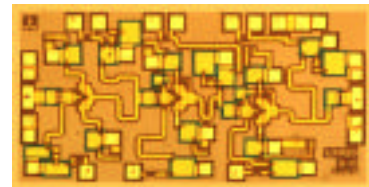
## FEATURES

- RF frequency : 24.0 to 27.0 GHz
- Super Low Noise NF=2.5dB (TYP.)
- Single voltage operation

## BLOCK DIAGRAM



## PHOTOGRAPH



## ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Values	Unit
Vd	Drain bias voltage	5	V
Id	Drain bias current	30	mA
Vg	Gate bias voltage	-	V
Pin	Maximum peak input power overdrive (Duration < 1sec)	TBD	dBm
Ta	Operating temperature range	TBD	°C

## TARGET SPECIFICATIONS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
Fop	Operating frequency range	On-wafer measurement	24.0		27.0	GHz
Gain	Small signal gain		17.0	18.0		dB
Delta gain	Small signal gain flatness			1.5		dB
NF	Noise figure			2.5		dB
VSWR in	Input VSWR				2.5:1	
VSWR out	Output VSWR				2.5:1	
P1dB	Output power at 1 dB compression		Freq=22GHz Vd=5V,Id=30mA		(5) TBD	
Output IP3	Output power at 3rd-order intercept point			(17) TBD		dBm
Vd	Drain bias voltage			5	V	
Id	Drain bias current			30	mA	
Vg	Gate bias voltage			No need	V	

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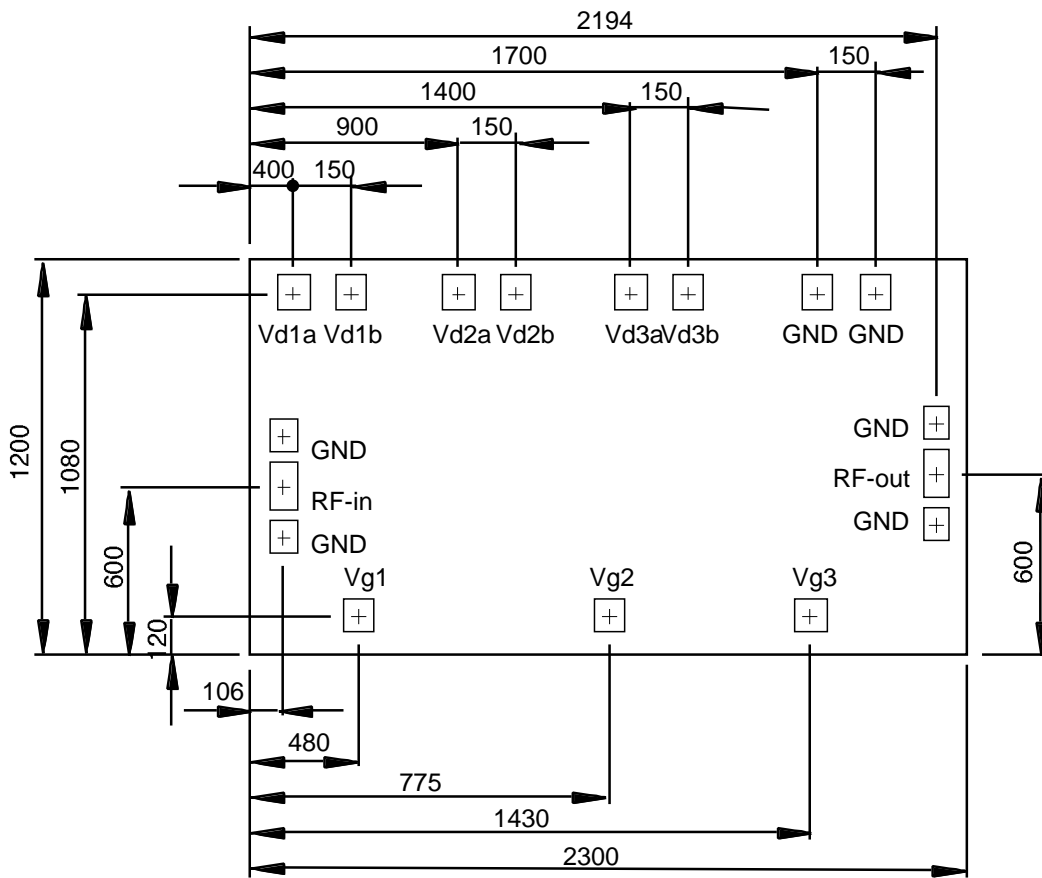
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## DIE SIZE AND BOND PAD LOCATION(UNIT : $\mu\text{m}$ )



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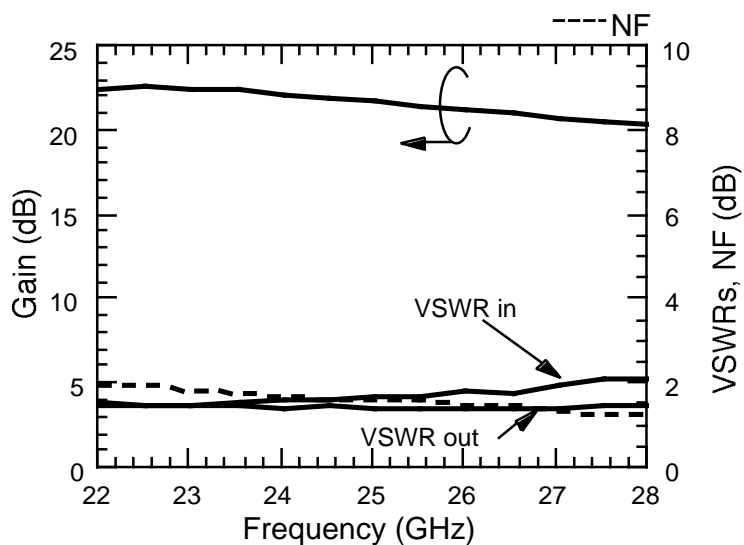
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## TYPICAL CHARACTERISTICS

### Small Signal Performances

( $V_d = 5.0 \text{ V}$ ,  $I_d = 30 \text{ mA}$ ,  $T_a = 25 \text{ }^\circ\text{C}$ )



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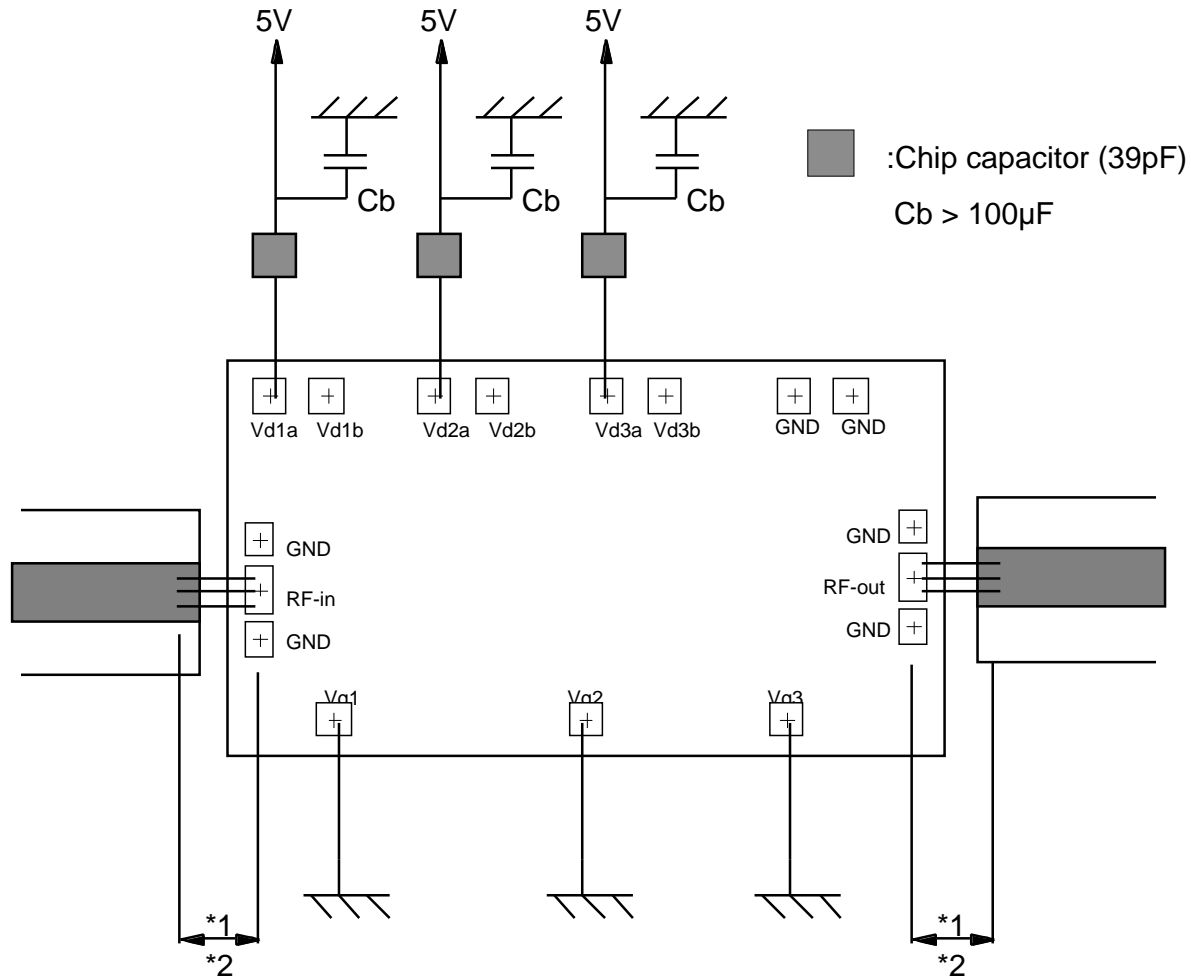
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## AN EXAMPLE OF TEST CIRCUIT



\*1 Length of bonding wire < 200  $\mu$ m

\*2 Number of bonding wire 3

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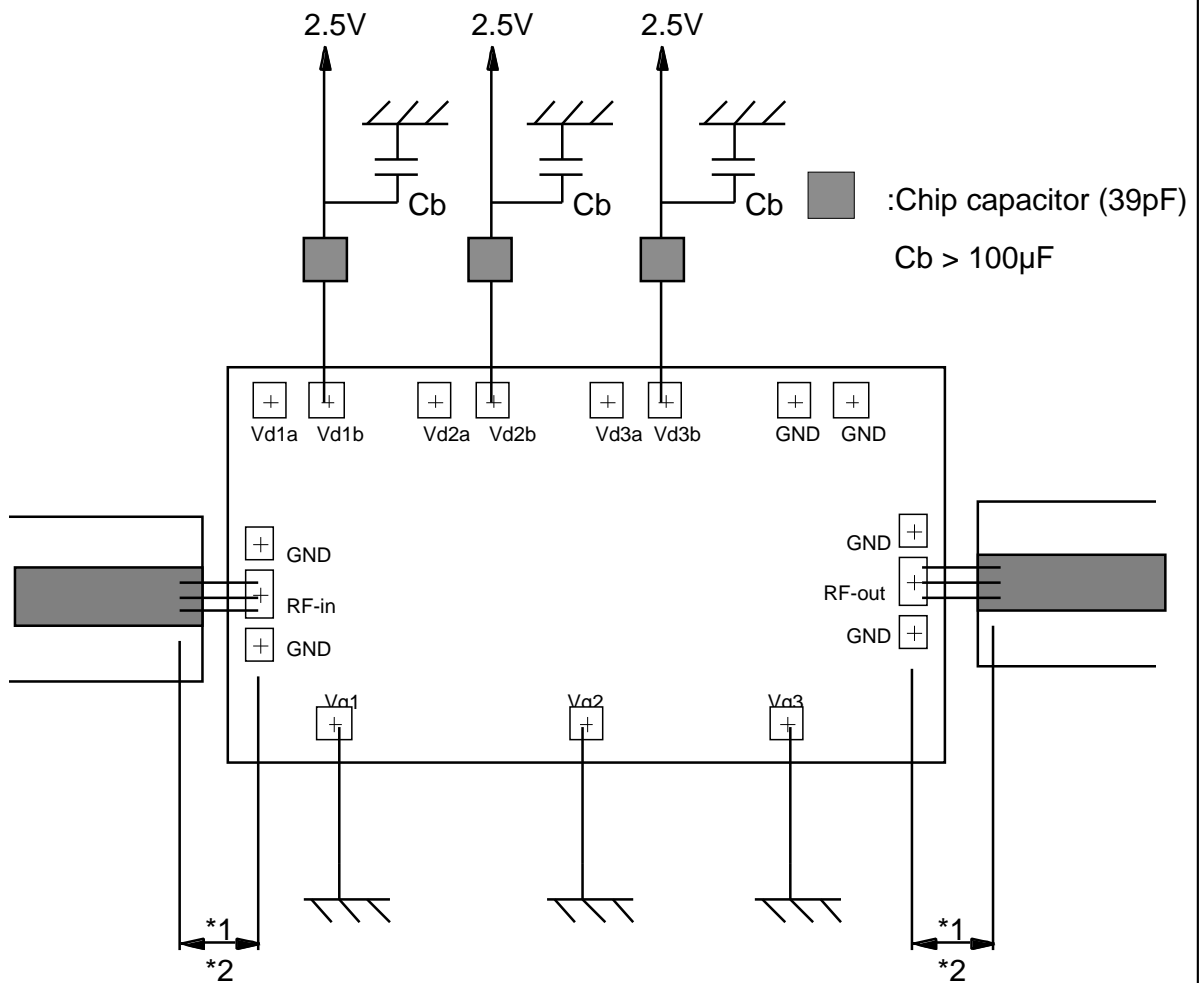
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